



### **Ordering Information**

BV <sub>DSS</sub> / BV <sub>DGS</sub>	R <sub>DS(ON)</sub> (max)	I <sub>D(ON)</sub> (min)	Order Number / Package			
			Die <sup>†</sup>			
60V	3.0Ω	2.0A	VN01506NW			
90V	3.0Ω	2.0A	VN1509NW			

<sup>†</sup> MIL visual screening available.

### **Features**

- □ Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- □ Low C<sub>ISS</sub> and fast switching speeds
- Excellent thermal stability
- Integral Source-Drain diode
- □ High input impedance and high gain
- Complementary N- and P-channel devices

### Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

## **Absolute Maximum Ratings**

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	BV <sub>DGS</sub>
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

\* Distance of 1.6 mm from case for 10 seconds.

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### Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Symbol	Parameter		Min	Тур	Max	Unit	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	VN1509	90			V	$V_{cs} = 0V, I_{D} = 1mA$
		VN1506	60				
V <sub>GS(th)</sub>	Gate Threshold Voltage		0.8		2.4	V	$V_{GS} = V_{DS}, I_D = 1mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature			-3.8	-5.5	mV/°C	$V_{GS} = V_{DS}, I_{D} = 1mA$
I <sub>GSS</sub>	Gate Body Leakage				100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I <sub>DSS</sub>	DSS Zero Gate Voltage Drain Current				1	μΑ	$V_{GS} = 0V, V_{DS} = Max Rating$
					100		$V_{GS} = 0V$ , $V_{DS} = 0.8$ Max Rating $T_A = 125^{\circ}C$
I <sub>D(ON)</sub>	ON-State Drain Current		0.5	1.0		A	$V_{GS} = 5V, V_{DS} = 25V$
			2.0	2.5			$V_{GS} = 10V, V_{DS} = 25V$
R <sub>DS(ON)</sub>	Static Drain-to-Source ON-State Resistance			3.0	5.0	Ω	$V_{GS} = 5V, I_{D} = 250mA$
				2.5	3.0		$V_{GS} = 10V, I_{D} = 1A$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			0.70	1	%/°C	$V_{GS} = 10V, I_{D} = 1A$
G <sub>FS</sub>	Forward Transconductance		300	450		mΩ	$V_{DS} = 25V, I_{D} = 0.5A$
C <sub>ISS</sub>	Input Capacitance			55	65	pF	$V_{GS} = 0V, V_{DS} = 25V$ f = 1 MHz
C <sub>OSS</sub>	Common Source Output Capacitance			20	25		
C <sub>RSS</sub>	Reverse Transfer Capacitance			5	8		
t <sub>d(ON)</sub>	Turn-ON Delay Time			3	5		
t <sub>r</sub>	Rise Time			5	8	ns	$V_{DD} = 25V$ $I_D = 1A$ $R_{GEN} = 25\Omega$
$t_{d(OFF)}$	Turn-OFF Delay Time			6	9		
t <sub>f</sub>	Fall Time			5	8		GEN
V <sub>SD</sub>	Diode Forward Voltage Drop		1.2	1.8	V	$V_{GS} = 0V, I_{SD} = 1.0A$	
t <sub>rr</sub>	Reverse Recovery Time			400		ns	$V_{GS} = 0V, I_{SD} = 1.0A$

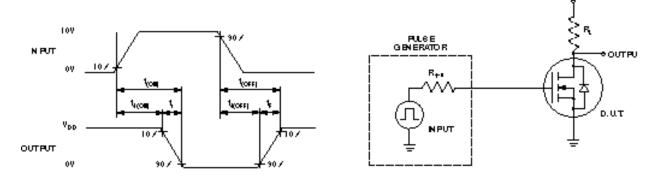
### Electrical Characteristics (@ 25°C unless otherwise specified)

Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

2. All A.C. parameters sample tested.

# **Switching Waveforms and Test Circuit**



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